

isc Silicon PNP Power Transistor**2SA818****DESCRIPTION**

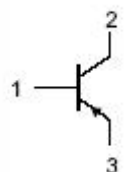
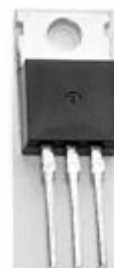
- Collector-Emitter Breakdown Voltage
: $V_{(BR)CEO} = -160V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC1628

APPLICATIONS

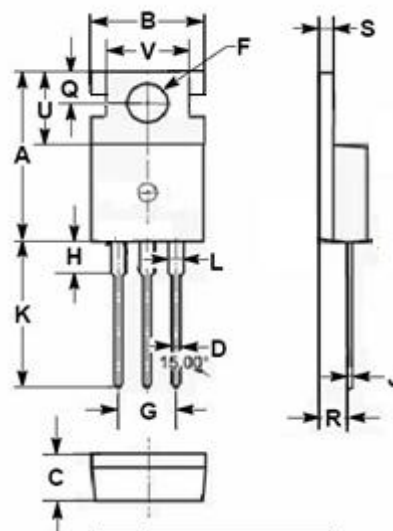
- Power amplifier applications
- Driver stage amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-50	mA
P_C	Total Power Dissipation @ $T_C=25^\circ\text{C}$	1	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



PIN 1. BASE
2. COLLECTOR
3. EMITTER
TO-220C package



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
O	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon PNP Power Transistor**2SA818****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA ; I _B = 0	-160			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA ; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -0.5A ; V _{CE} = -5V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -180V ; I _E = 0			-10.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-10.0	μ A
h _{FE}	DC Current Gain	I _C = -10mA ; V _{CE} = -5V	70		240	
f _T	Current-Gain—Bandwidth Product	I _C = -0.1A; V _{CE} = -5V		120		MHz